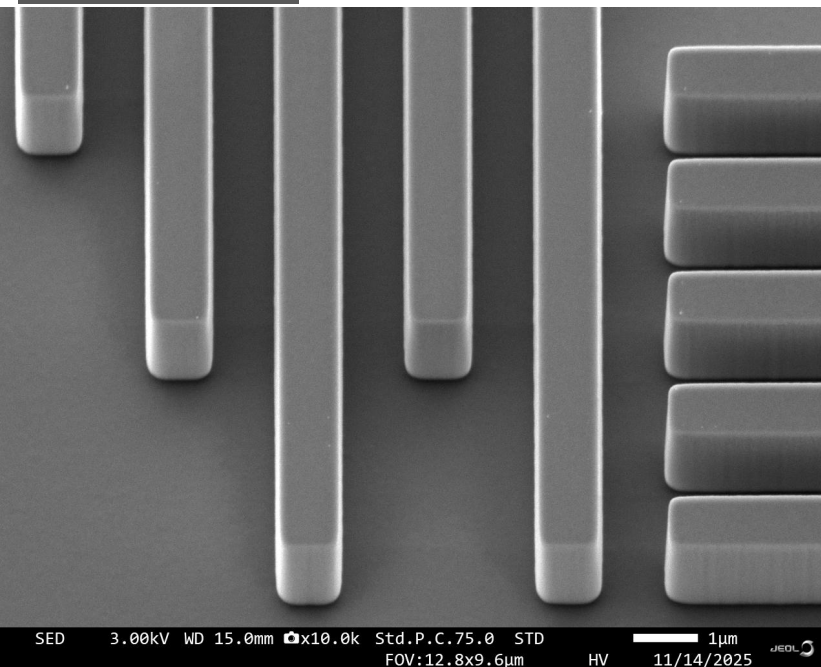


Si Etch Analogous Processes

Fluorine ICP: SiVertHFv2

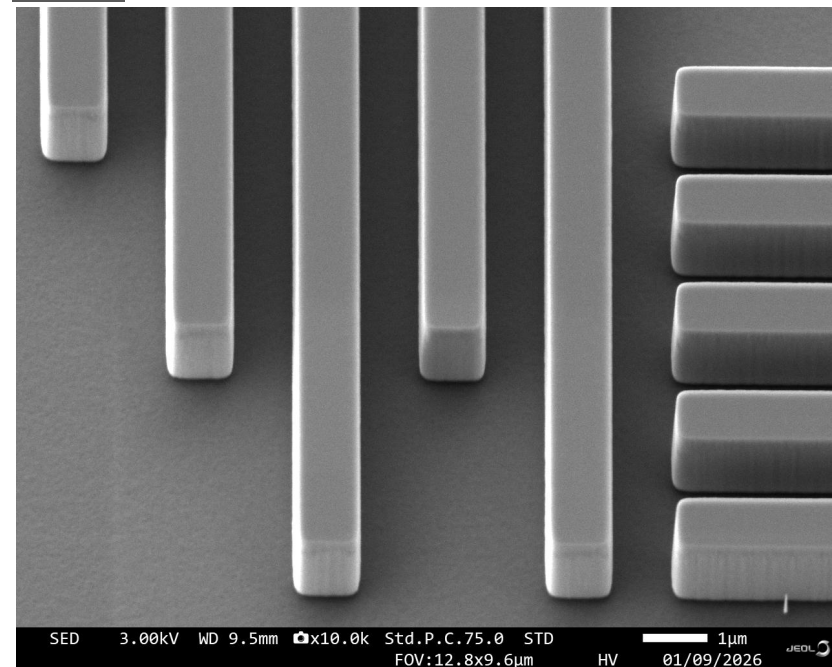


Smooth, Vertical, E.R. uniformity is within 5% on wafer

20mT, 18/950W, C4F8/SF6/CF4=120/48/54sccm

E.R. = 355.4nm/min, Selectivity (to UV6) = 4.8

DSE: SF6-C4F8-CF4 Si Etch v1



Smooth, Vertical, E.R. uniformity is within 5% on wafer

12mT, 20/850W, C4F8/SF6/CF4=68.3/32.5/32.4sccm

E.R. = 339.4nm/min, Selectivity (to UV6) = 4.9

SiO₂ Etch Analogous Processes

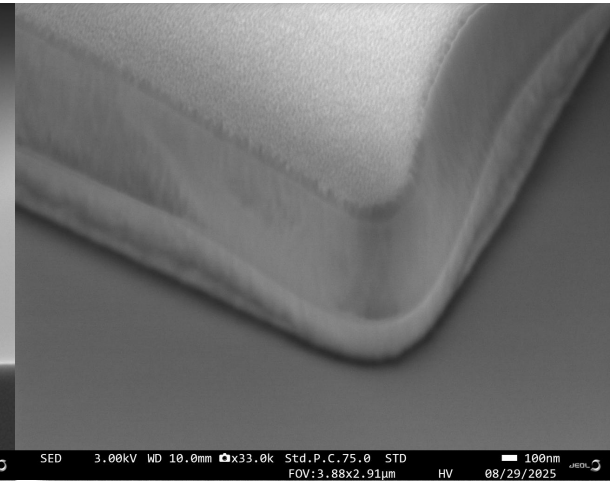
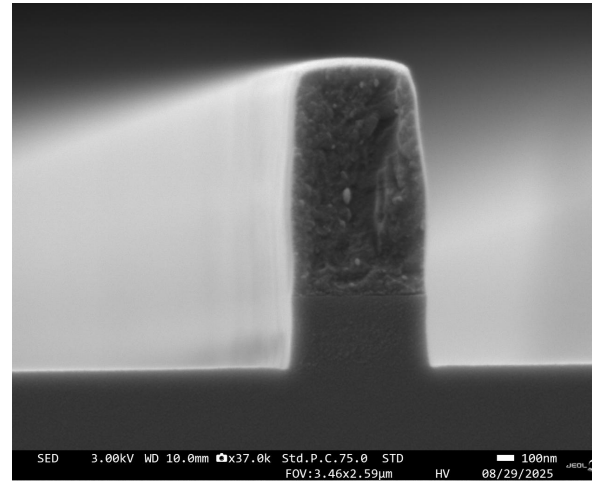
Fluorine ICP:

SiO₂ Etch-50W

3.8mT, 50/900W, CHF₃/CF₄=10/30

E.R. = **284.6nm/min**, Selectivity (to SPR955) = **1.2**

Vertical/Smooth



DSE:

CF₄-C₄F₈ SiO₂ Etch v1

3mT, 70/800W, C₄F₈/CF₄=7.5/32.5sccm

E.R. = **270nm/min**, Selectivity (to SPR955) = **1.3**

Vertical/Smooth

